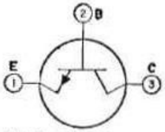
TRANSISTOR

2N1010



Germanium n-p-n type used in low-noise small-signal audio-frequency amplifier applications. It is used in input stages of audio-frequency amplifiers operating from extremely small input signals, such as high-fidelity preamplifiers, tape-recorder amplifiers, microphone preamplifiers, and hearing aids, in which low noise is an important design consideration. JEDEC No. TO-1 package; outline 4, Outlines Section.

MAXIMUM RATINGS

Collector-to-Base Voltage (with emitter open)	10 max	volts
Collector-to-Emitter Voltage	10 max	volts
Emitter-to-Base Voltage (with collector open)	10 max	volts
Collector Current	2 max	ma
Emitter Current	−2 max	ma
Transistor Dissipation:		
At ambient temperatures up to 55°C	20 max	mw
Ambient-Temperature Range:		
Operating	−65 to 55	°C
Storage	−65 to 85	°C

CHARACTERISTICS

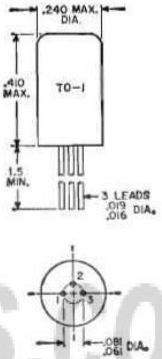
Collector-Cutoff Current (with collector-to-base volts = 10 and emitter current = 0)	10 max	μa
Emitter-Cutoff Current (with emitter-to-base volts = 2.5 and collector current = 0)	6 max	μa

In Common-Base Circuit

Small-Signal Forward-Current-Transfer-Ratio Cutoff Frequency (with collector-to-base volts = 3.5 and collector ma = 0.3)	2	Mc

In Common-Emitter Circuit

Small-Signal Forward Current-Transfer Ratio at 1 kilocycle (with collector-to-emitter volts = 3.5 and collector ma = 0.3)	35	
Noise Figure (with generator resistance = 1000 ohms and integrated noise bandwidth = 15 kilocycles)	5	db



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